





DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Notes 2 and 3)

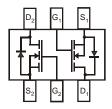
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

SOT363



Top View



Top View Internal Schematic

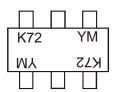
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DW-7-F	SOT363	3,000/Tape & Reel
2N7002DW-13-F	SOT363	10,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K72 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	K	L	М	N	Р	R		Υ	Z	Α	В	С	D	Е
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteris	etic	Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	60	V
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

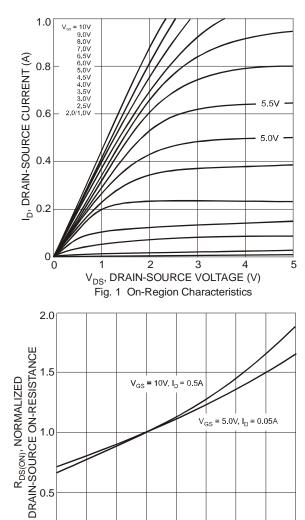
Characteristic	Symbol	Value	Units
Total Power Dissipation	Б	200	mW
Derating above T _A = 25°C (Note 5)	PD	1.60	mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

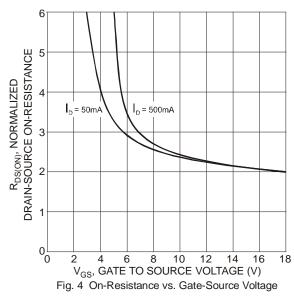
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}			1.0 500	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		$V_{GS(th)}$	1.0		2.0	>	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ $T_J = 25^{\circ}C$	R _{DS} (ON)		3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
	@ T _J = 125°C	1 120 (011)		4.4	13.5		$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g FS	80	_		mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS (Note 7)					ā.		
Input Capacitance		C _{iss}		22	50	рF	
Output Capacitance				11	25	рF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}		2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Note 7)			•	•		•	
Turn-On Delay Time		t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V$, $I_D = 0.2A$, $R_L = 150\Omega$,
Turn-Off Delay Time		t _{D(OFF)}		11	20	ns	$V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



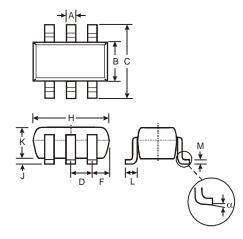




Package Outline Dimensions

-30

-55



) -5 20 45 70 95 1 T_j, JUNCTION TEMPERATURE (°C)

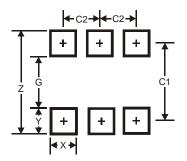
Fig. 3 On-Resistance vs. Junction Temperature

120

SOT363							
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
C	2.00	2.20					
D	0.65	Тур					
F	0.40 0.45						
Н	1.80	2.20					
7	0	0.10					
K	0.90 1.00						
L	0.25 0.40						
М	0.10	0.22					
α	0° 8°						
All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

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